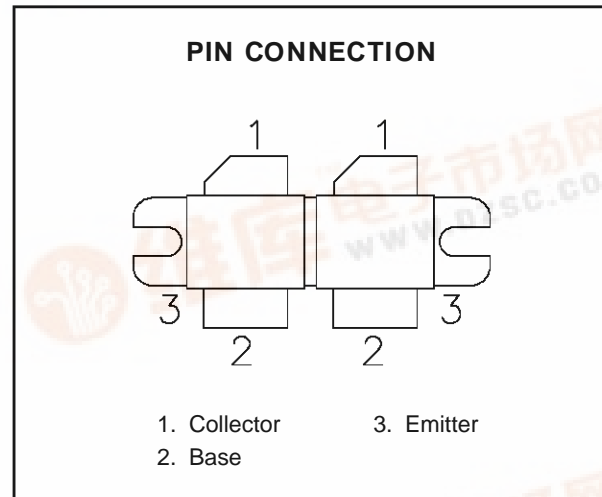
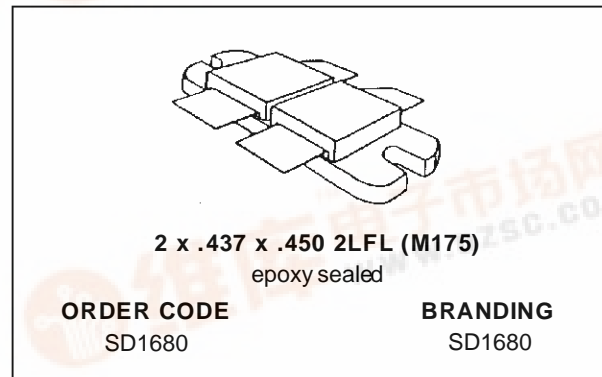




**SD1680**

**RF & MICROWAVE TRANSISTORS  
800/900 MHz APPLICATIONS**

- 915 - 960 MHz
- 24 VOLTS
- CLASS AB PUSH PULL
- INTERNAL INPUT MATCHING
- DESIGNED FOR HIGH POWER LINEAR OPERATION
- HIGH SATURATED POWER CAPABILITY
- GOLD METALLIZATION FOR HIGH RELIABILITY
- DIFFUSED EMITTER BALLAST RESISTORS
- COMMON EMITTER CONFIGURATION
- $P_{OUT} = 100 \text{ W MIN. WITH } 7.0 \text{ dB GAIN}$



**DESCRIPTION**

The SD1680 is a gold metallized epitaxial silicon NPN planar transistor using diffused emitter ballast resistors for high linearity Class AB operation in cellular base station applications.

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}\text{C}$ )

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	30	V
$V_{EBO}$	Emitter-Base Voltage	3.0	V
$I_C$	Device Current	25	A
$P_{DISS}$	Power Dissipation	310	W
$T_J$	Junction Temperature	+200	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature	- 55 to +150	$^{\circ}\text{C}$

**THERMAL DATA**

$R_{\theta(j-c)}$	Junction-Case Thermal Resistance	0.55	$^{\circ}\text{C/W}$
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# SD1680

## ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)

### STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV <sub>CBO</sub>	I <sub>C</sub> = 100mA	I <sub>E</sub> = 0mA	60	—	—	V
BV <sub>CEO</sub>	I <sub>C</sub> = 100mA	I <sub>B</sub> = 0mA	30	—	—	V
BV <sub>EBO</sub>	I <sub>E</sub> = 50mA	I <sub>C</sub> = 0mA	3.0	—	—	V
I <sub>CES</sub>	V <sub>CE</sub> = 28V	I <sub>E</sub> = 0mA	—	—	10	mA
h <sub>FE</sub>	V <sub>CE</sub> = 5V	I <sub>C</sub> = 3A	15	—	70	—

Tested Per Side

### DYNAMIC

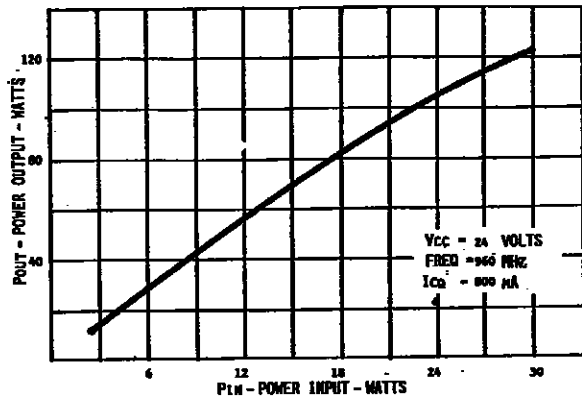
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P <sub>OUT</sub> *	f = 900 MHz	V <sub>CE</sub> = 24 V	I <sub>CQ</sub> = 2 x 300 mA	120	—	—	W
G <sub>P</sub> *	f = 900 MHz	V <sub>CE</sub> = 24 V	I <sub>CQ</sub> = 2 x 300 mA	7.0	—	—	dB
IMD**	f = 900 MHz	V <sub>CE</sub> = 24 V	I <sub>CQ</sub> = 2 x 300 mA	—	-32	—	dBc
η <sub>C</sub>	f = 900 MHz	V <sub>CE</sub> = 24 V	I <sub>CQ</sub> = 2 x 300 mA	45	—	—	%
C <sub>OB</sub>	f = 1 MHz	V <sub>CB</sub> = 28 V		—	—	100	pF

Note: \* @ 1 dB Compression

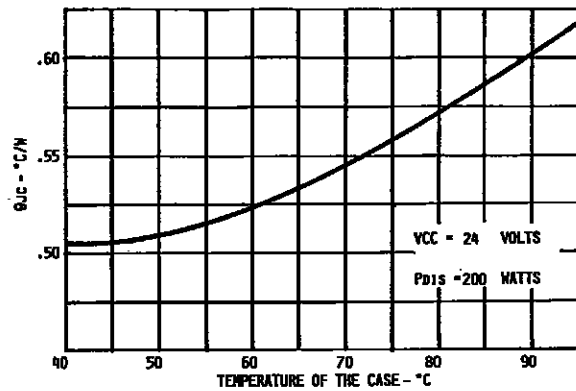
\*\* P<sub>OUT</sub> = 100W PEP, Δ F = 400KHz (2 tones)

## TYPICAL PERFORMANCE

POWER OUTPUT vs POWER INPUT

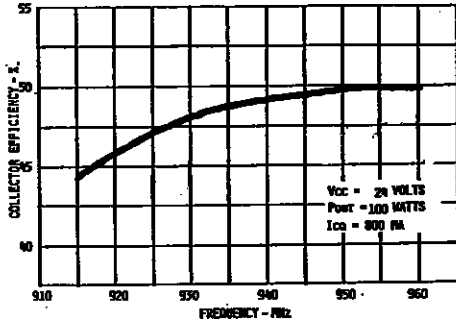


THERMAL RESISTANCE vs CASE TEMPERATURE

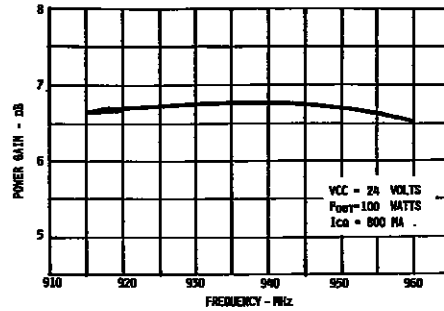


TYPICAL PERFORMANCE (cont'd)

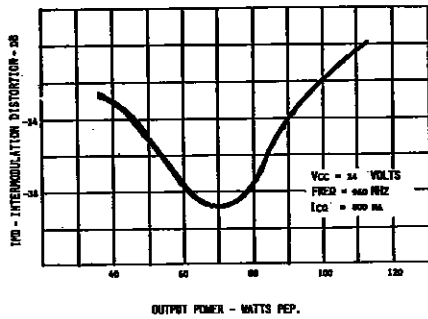
COLLECTOR EFFICIENCY vs FREQUENCY



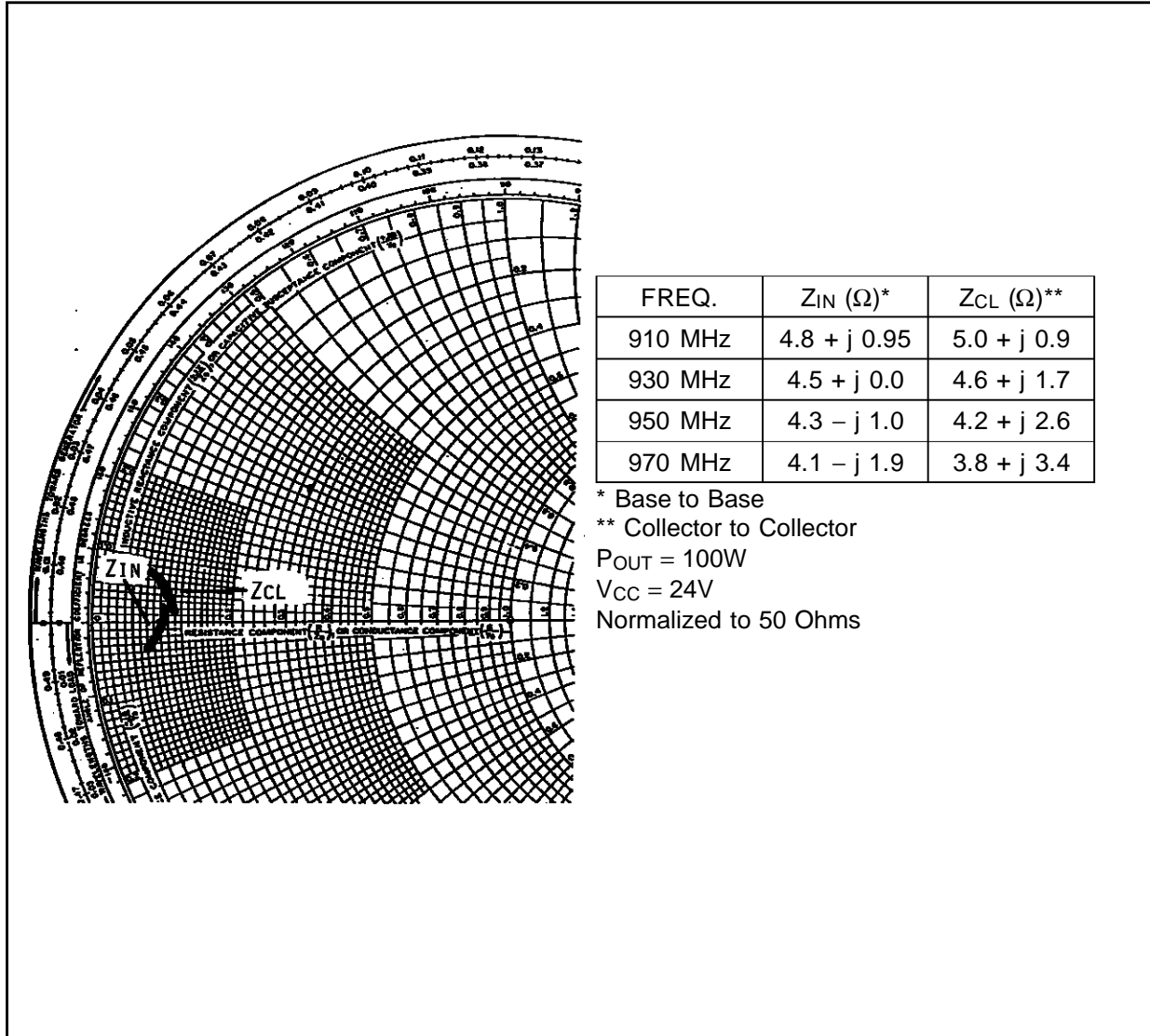
BROADBAND POWER GAIN vs FREQUENCY



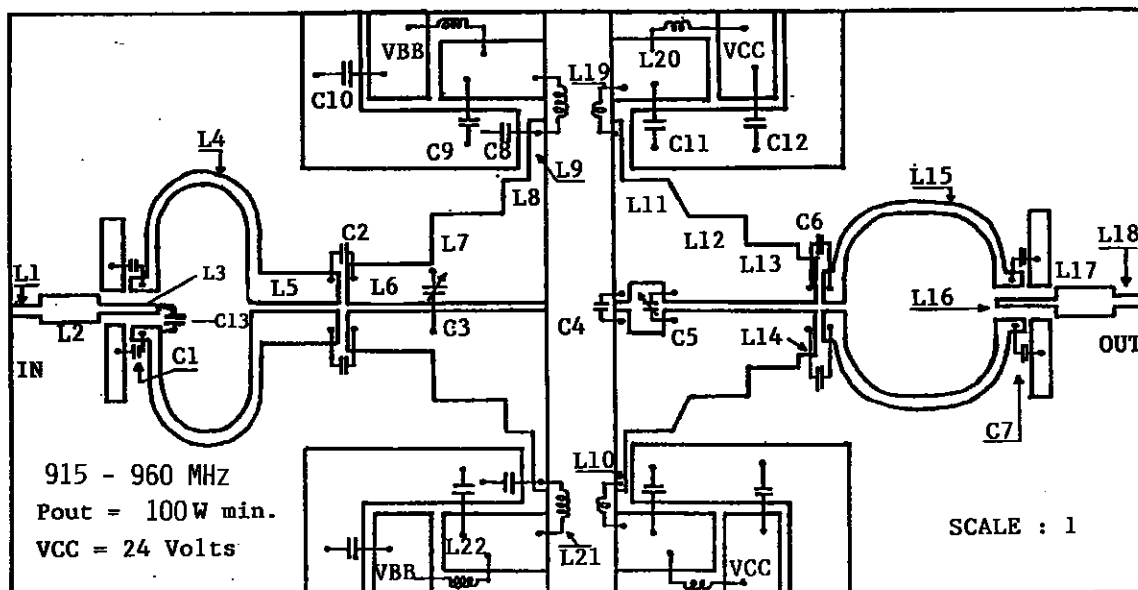
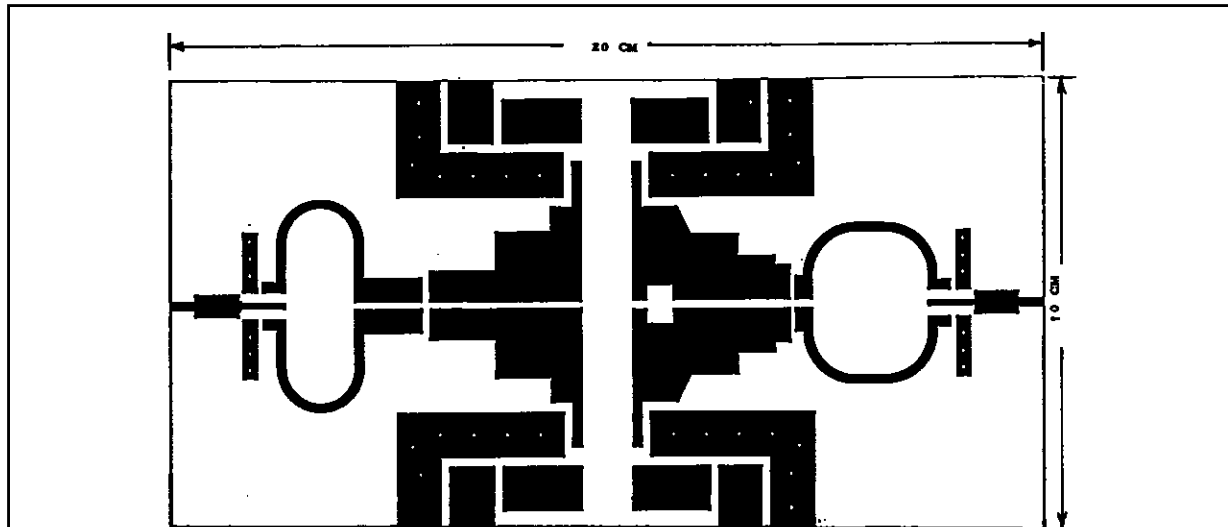
INTERMODULATION DISTORTION vs POWER OUTPUT



IMPEDANCE DATA



## TEST CIRCUIT



B1, B2 : Coaxial Cable 25, 43mm

C1, C2 : 330pF, ATC 100B

C3 : .8 - 8.0pF Johanson Gigatrim

C4 : 2 x 3.6pF + 1.6pF ATC 100B

C5 : 3.3pF ATC 100B + .8 - 8.0pF  
 Johanson Gigatrim

C6, C7 : 330pF, ATC 100B

C8 : 120pF ATC 100B

C9 : 1.5nF, ATC 100B

C10 : 10nF + 47 $\mu$ F, 63V

C11 : 1.5nF, ATC 100B + 10nF

C12 : 470pF + 1.5nF, ATC 100B + 100mF, 63V

C13 : .4 - 4pF Johanson Gigatrim

L1, L18 : Printed Line 50 $\Omega$

L2, L17 : Printed Line 26.7 $\Omega$  10mm

L3, L16 : Printed Line 60 $\Omega$  10.5mm

L4, L15 : Printed Line 50 $\Omega$  43mm

L5 : Printed Line 25 $\Omega$  13.5mm

L6 : Printed Line 21 $\Omega$  15mm

L7 : Printed Line 10.5 $\Omega$  12.5mm

L8 : Printed Line 8 $\Omega$  7.5mm

L9, L10 : Printed Line 50 $\Omega$  10mm

L11 : Printed Line 9.5 $\Omega$  10.5mm

L12 : Printed Line 11 $\Omega$  14.5mm

L13 : Printed Line 15.5 $\Omega$  8.5mm

L14 : Printed Line 19 $\Omega$  3.5mm

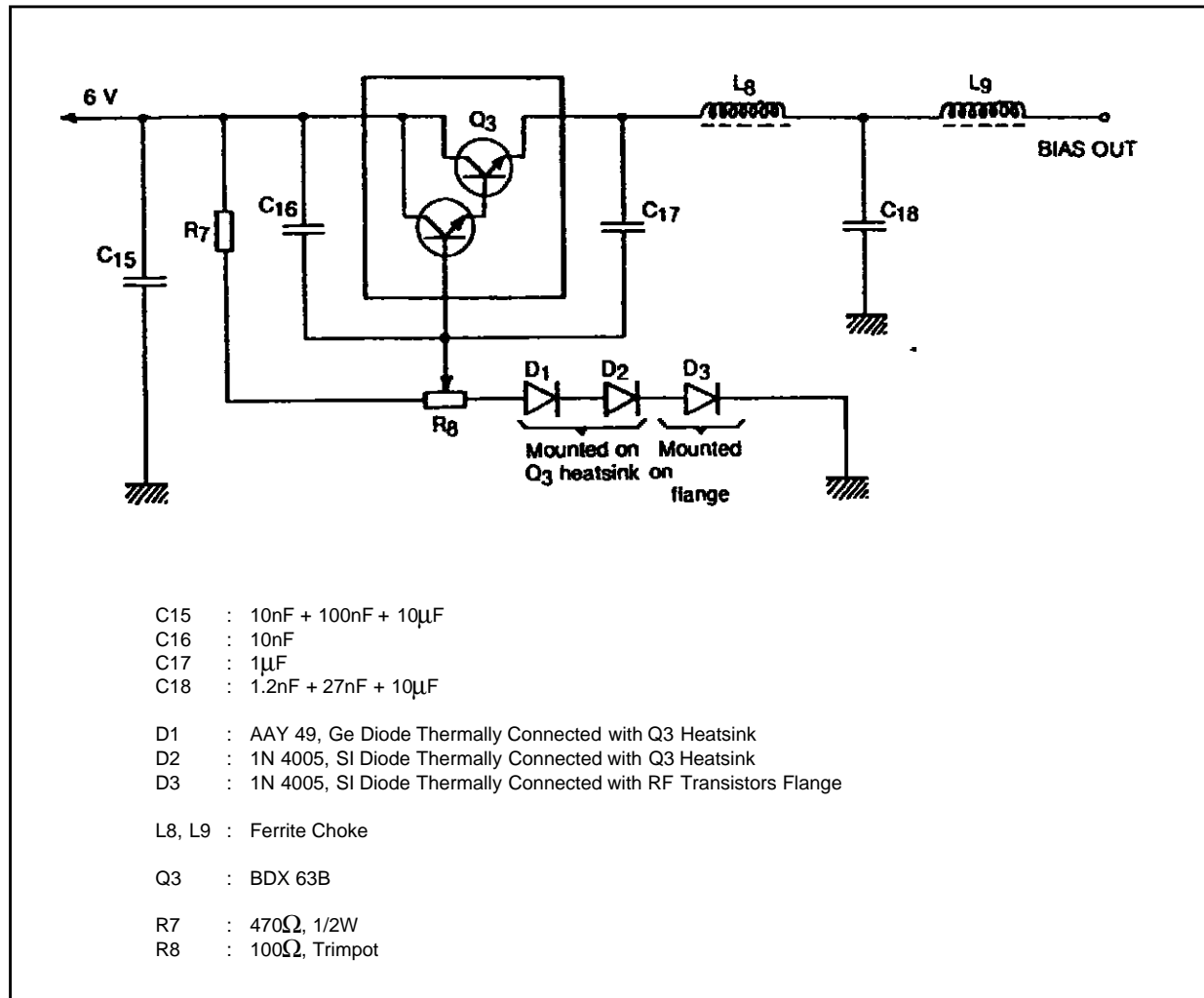
L19 : 2 Turns, #16 AWG

L20 : 2 Turns, #16 AWG

L21, L22 : 12 Turns, #22 AWG

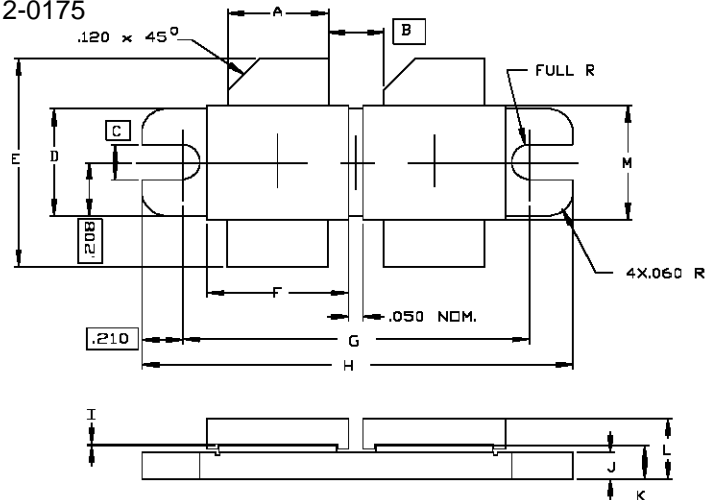
Substrate: Teflon Glass,  $\epsilon_r = 2.55$ , 30Mils Thick

## BIAS VOLTAGE SOURCE



## PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0175



SGS-THOMSON MICROELECTRONICS		CONT'D			
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.373/9,47	.385/9,78	K	.115/2,92	.135/3,43
B	.190/4,83		L		.250/6,35
C	.130/3,30		M	.445/11,30	.455/11,56
D	.411/10,44	.421/10,69			
E	.825/20,96	.865/21,97			
F	.525/13,34	.535/13,59			
G	1.255/31,88	1.265/32,13			
H	1.675/42,55	1.685/42,80			
I	.002/0,05	.006/0,15			
J	.095/2,41	.105/2,67			

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